

REMARKS

Claims 1-21 are pending. By this Amendment, claims 1 -14, 17, 20 and 21 are amended for further clarity only. No new matter is added. Reconsideration of the above amendments and following remarks is respectfully requested.

Applicants gratefully acknowledge that claims 4-6, 10-13, and 18-21 contain allowable subject matter. However, Applicants respectfully submit that all of claims 1-21 are allowable as noted below.

In the Office Action, claim 9 is rejected under 35 U.S.C. §112 second paragraph, as being indefinite. Claim 9 has been amended to obviate the objection. Accordingly, Applicants requests withdrawal of the rejection of claim 9 under §112.

In the Office Action, claims 1 and 14-17 are rejected under 35 U.S.C. §102(e) as being anticipated by (U.S. Patent No. 5,616,935) to Koyama et al. This rejection is respectfully traversed.

Koyama et al. teach that making one channel length shorter than another channel length can reduce the threshold voltage required in a thin film transistor (TFT). Koyama et al. even in Fig. 2a, do not teach nor anticipate wherein "at least one of the component parts being formed from a conductive film or a semiconductor film with a heat dissipating extension", as claimed in claim 1. Accordingly, claim 1 and claims 14-17 depending therefrom are not anticipated by Koyama. Withdrawal of the rejections of claims 1 and 14-17 under 35 U.S.C. §102(e) is respectfully requested.

In the Office Action, claims 1-3, 7, 8, and 17 are rejected under 35 U.S.C. §102(e) as being anticipated by (U.S. Patent No. 5,623,155) to Kerber et al. The rejection is respectfully traversed.

Kerber et al. teach in col. 1, lines 64-col. 2, line 1 that "one end of the ridge does not project beyond, or only slightly projects beyond, the channel region. Undesirable, additional capacitances between the gate electrode and the source and drain regions are thus kept optimally small." Thus, Kerber et al. teach away from "at least one of the component parts being formed from a conductive film or a semiconductor film with a heat dissipating extension", as claimed in claim 1. Accordingly, claim 1 and claims 2, 3, 7, 8 and 17 depending therefrom are not anticipated by Kerber. Withdrawal of the rejections of claims 1-3, 7, 8 and 17 under 35 U.S.C. §102(e) is respectfully requested.

In the Office Action, claims 1-3, 9, 14 and 17 are rejected under 35 U.S.C. §102(e) as being anticipated by (U.S. Patent No. 5,920,085) to Han et al. The rejection is respectfully traversed.

Han et al. teach a method for forming a field effect transistors which are capable of high saturation current and low leakage current, which may only require a single implantation step and which may be formed in a self-lined manner to provide a symmetrical transistor. Han et al. do not teach anything about a "conductive film or a semiconductor film with a heat dissipating extension", as claimed in claim 1. Accordingly, claim 1 and claims 2, 3, 9, 14 and 17 depending therefrom are not anticipated by Han. Withdrawal of the rejection of claims 1-3, 9, 14 and 17 under 35 U.S.C. §102(e) is respectfully requested.

In the Office Action, claims 1, 9, 15 and 16 are rejected under 35 U.S.C. §102(e) as being anticipated by (U.S. Patent No. 5,959,313) to Yamazaki et al. The rejection is respectfully traversed.

Yamazaki et al. teach a thin film transistor which is not effected by crystal grain boundaries. Yamazaki et al. does not teach or anticipate "at least one of the component parts being formed from a conductive film or a semiconductor film with a heat dissipating

extension", as claimed in claim 1. Accordingly, claim 1 and claims 9, 15 and 16 depending therefrom are not anticipated by Yamazaki. Withdrawal of the rejection of claims 1, 9, 15 and 16 under 35 U.S.C. §102(e) is respectfully requested.

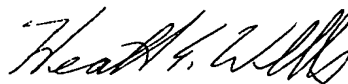
In the Office Action, claims 1-3, 14 and 17 are rejected under 35 U.S.C. §102(e) as being anticipated by U.S. Patent No. 6,064,090 to Miyamoto et al. The rejection is respectfully traversed.

Miyamoto et al. teach a semiconductor device having stable characteristics with suppressed source/drain leak current. Miyamoto et al. do not teach or suggest any means for wherein "at least one of the component parts being formed from a conductive film or a semiconductor film with a heat dissipating extension ", as claimed in claim 1. Accordingly, claim 1 and claims 2, 3, 14 and 17 depending therefrom are not anticipated by Miyamoto. Withdrawal of the rejection of claims 1-3, 14 and 17 under 35 U.S.C. §102(e) is respectfully requested.

For at least the above reasons, it is respectfully submitted that the application is in condition for allowance. Favorable reconsideration and prompt allowance are therefore respectfully requested.

Should the Examiner believe anything further is desirable in order to place this application in even better condition for allowance, the Examiner is invited to contact Applicants' undersigned representative at the telephone number listed below.

Respectfully submitted,



James A. Oliff  
Registration No. 27,075

Heath E. Wells  
Registration No. 43,257

JAO:HEW/amw

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OLIFF & BERRIDGE, PLC  
P.O. Box 19928  
Alexandria, Virginia 22320  
Telephone: (703) 836-6400